

RoHS Compliant Product
 A suffix of "-C" specifies halogen and lead-free

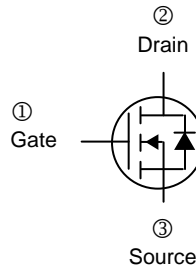
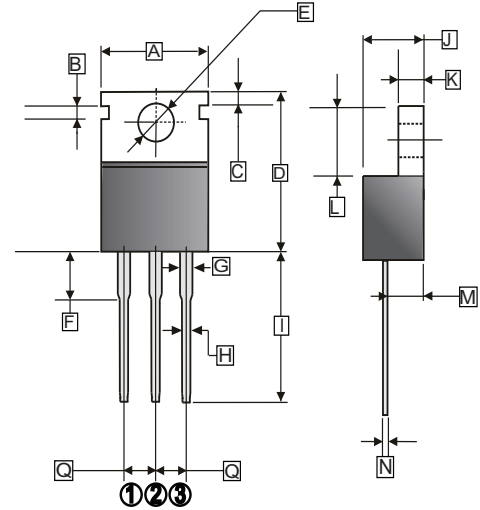
DESCRIPTION

The N-Channel MOSFET is used an advanced termination scheme to provide enhanced voltage-blocking capability without degrading performance over time. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance. This device is well suited for high efficiency switched mode power suppliers, active power factor correction, electronic lamp ballasts based half bridge topology.

FEATURES

- Robust high voltage termination
- Avalanche energy specified
- Diode is characterized for use in bridge circuits
- Source to Drain diode recovery time comparable to a discrete fast recovery diode.

TO-220Y



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	-	10.6	I	12.70	14.70
B	1.58	1.82	J	3.60	4.80
C	1.20	1.45	K	1.14	1.40
D	14.22	16.50	L	5.84	6.86
E	3.50	4.00	M	2.03	2.90
F	2.70	3.30	N	0.35	0.64
G	1.20	1.78	Q	2.34	2.74
H	0.50	1.00			

ABSOLUTE MAXIMUM RATINGS ($T_c=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Ratings	Unit
Drain-Source Voltage	V_{DS}	600	V
Gate-Source Voltage	V_{GS}	± 30	V
Continuous Drain Current	I_D	4.1	A
Pulsed Drain Current	I_{DM}	16.4	A
Power Dissipation ²	P_D	98	W
Derating factor above 25°C		0.78	W / °C
Single Pulsed Avalanche Energy ¹	E_{AS}	262	mJ
Repetitive Avalanche Energy ²	E_{AR}	3.9	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	150, -55 ~ 150	°C
Thermal Resistance Rating			
Maximum Junction to Ambient ¹	$R_{\theta JA}$	62.5	°C / W
Maximum Junction to Case	$R_{\theta JC}$	1.28	

Notes:

1. $L=26\text{mH}$, $I_{AS}=4.1\text{A}$, $V_{DD}=50\text{V}$, $R_G=50\Omega$, Starting $T_J=25^\circ\text{C}$
2. Repetitive Rating: Pulse width limited by maximum junction temperature.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Gate-Threshold Voltage	V _{GS(th)}	2	-	4	V	V _{DS} =V _{GS} , I _D =250μA
Drain-Source On-Resistance	R _{DS(ON)}	-	2.0	2.5	Ω	V _{GS} =10V, I _D =2.05A
Drain-Source Breakdown Voltage	BV _{DSS}	600	-	-	V	V _{GS} =0, I _D =250μA
Zero Gate Voltage Drain Current	I _{DSS}	-	-	10	μA	V _{DS} =600V, V _{GS} =0
Gate-Body Leakage Current, Forward	I _{GSSF}	-	-	100	nA	V _{GS} =30V, V _{DS} =0
Gate-Body Leakage Current, Reverse	I _{GSSR}	-	-	-100	nA	V _{GS} =-30V, V _{DS} =0
Dynamic						
Total Gate Charge ^{1,2}	Q _g	-	19	-	nC	V _{DS} =480V, I _D =4.1A, V _{GS} =10V
Gate-Source Charge ^{1,2}	Q _{gs}	-	2.9	-		
Gate-Drain Charge ^{1,2}	Q _{gd}	-	8.2	-		
Turn-on Delay Time ^{1,2}	T _{d(on)}	-	25	-	nS	V _{DD} =300V, I _D =4.1A, R _G =25Ω
Rise Time ^{1,2}	T _r	-	54	-		
Turn-off Delay Time ^{1,2}	T _{d(off)}	-	120	-		
Fall Time ^{1,2}	T _f	-	34	-		
Input Capacitance	C _{iss}	-	570	-	pF	V _{DS} =25V, V _{GS} =0, f=1.0MHz
Output Capacitance	C _{oss}	-	64	-		
Reverse Transfer Capacitance	C _{rss}	-	14	-		
Maximum Continuous Drain-Source Diode Forward Current	I _S	-	-	4.1	A	
Maximum Pulsed Drain-Source Diode Forward Current	I _{SM}	-	-	16.4	A	
Drain-Source Diode Forward Voltage	V _{SD}	-	-	1.4	V	V _{GS} =0, I _S =4A
Reverse Recovery Time ¹	T _{rr}	-	560	-	nS	V _{GS} =0, I _S =4.1A, dI _F / dt = 100A / μs
Reverse Recovery Charge ¹	Q _{rr}	-	1.78	-	μC	

Notes:

1. Pulse Test: Pulse width < 300us, Duty cycle ≤ 2%.
2. Basically not affected by working temperature.

CHARACTERISTIC CURVE

Fig 1. On-State Characteristics

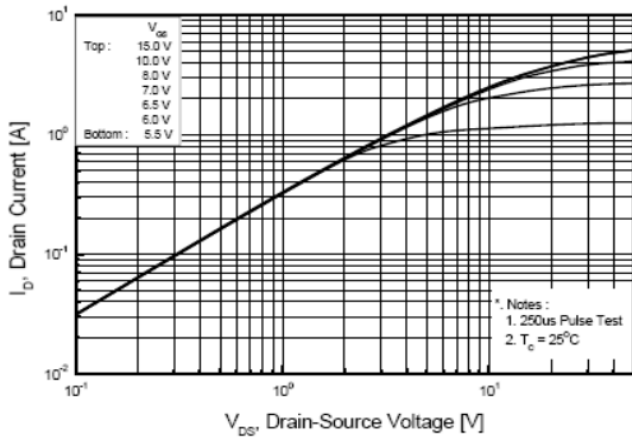


Fig 2. Transfer Characteristics

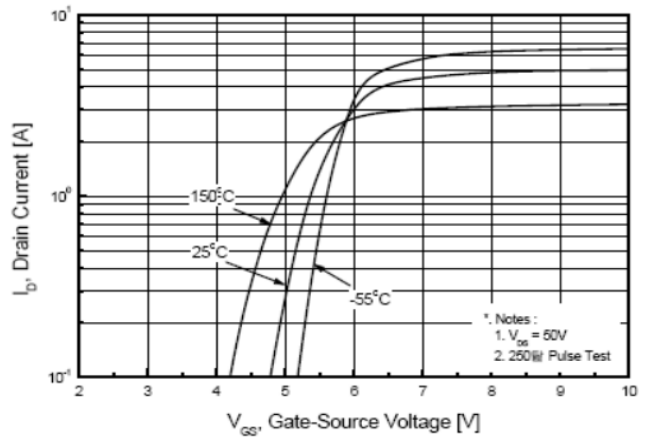


Fig 3. On Resistance Variation vs. Drain Current and Gate Voltage

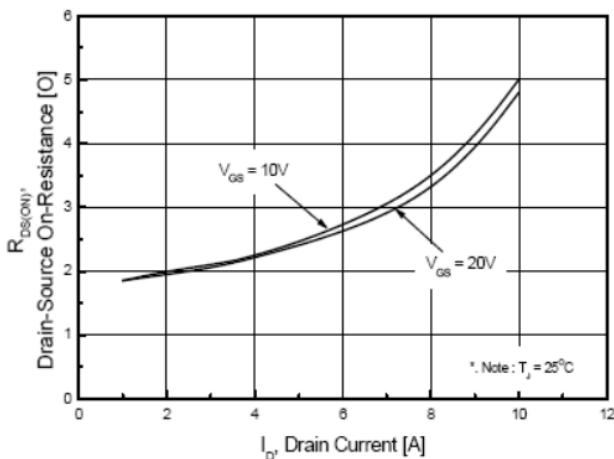


Fig 4. On State Current vs. Allowable Case Temperature

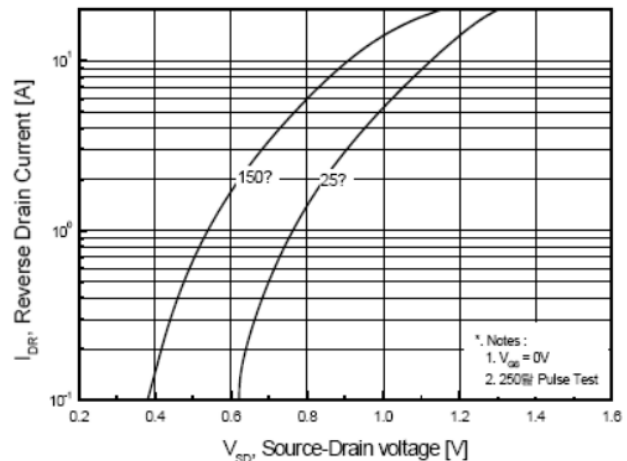


Fig 5. Capacitance Characteristics (Non-Repetitive)

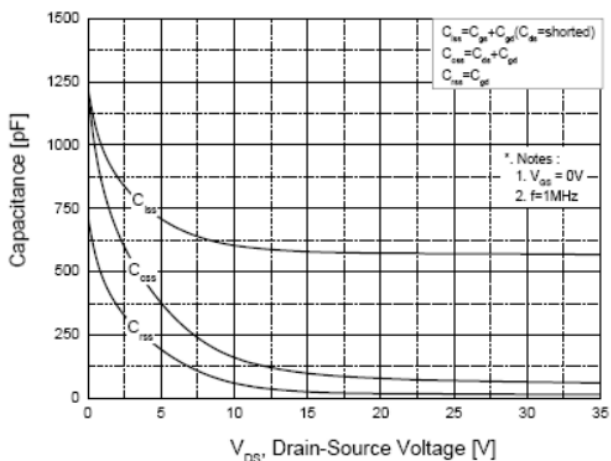
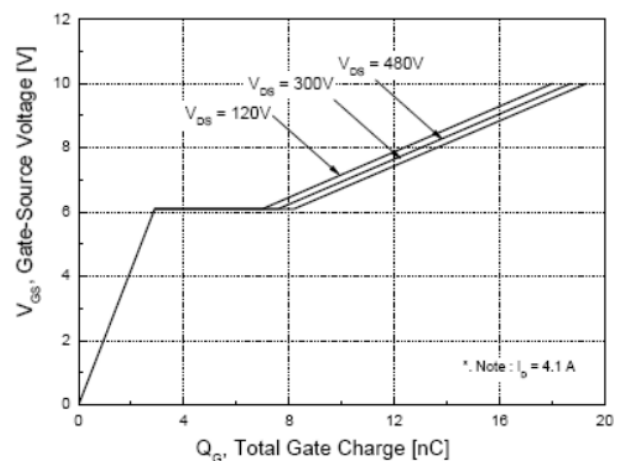


Fig 6. Gate Charge Characteristics



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Fig 7. Breakdown Voltage Variation vs. Junction Temperature

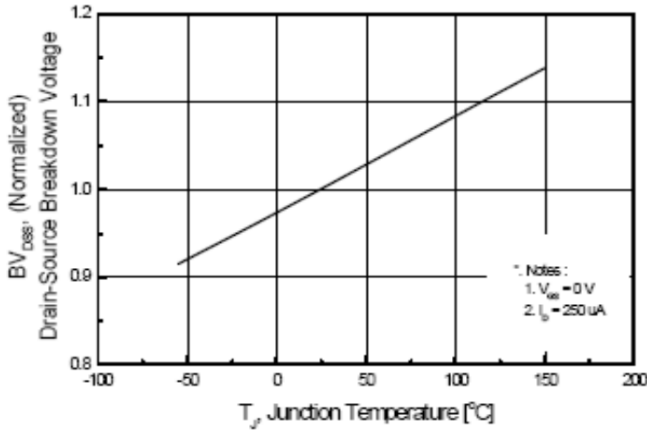


Fig 8. On-Resistance Variation vs. Junction Temperature

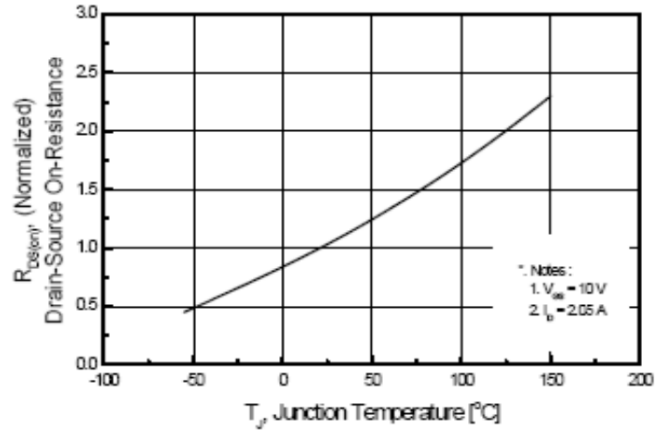


Fig 9. Maximum Safe Operating Area (TO-220)

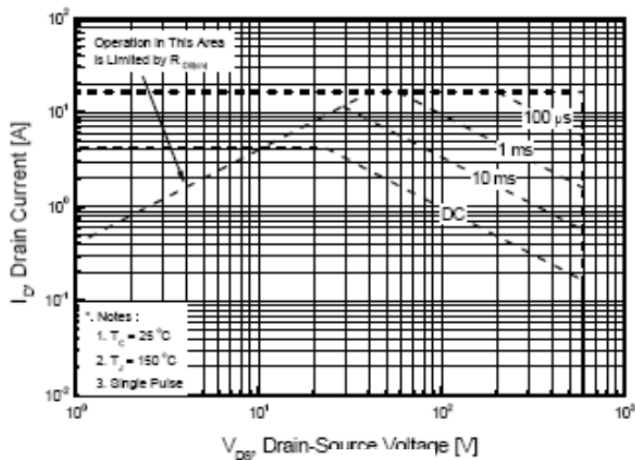


Fig 10. Maximum Drain Current vs. Case Temperature. (TO220)

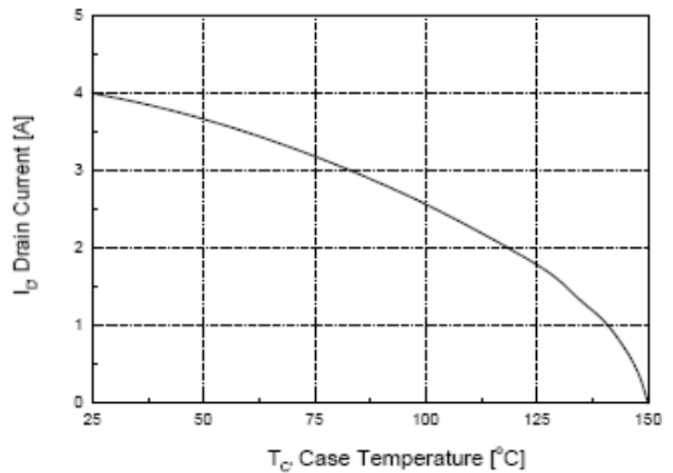
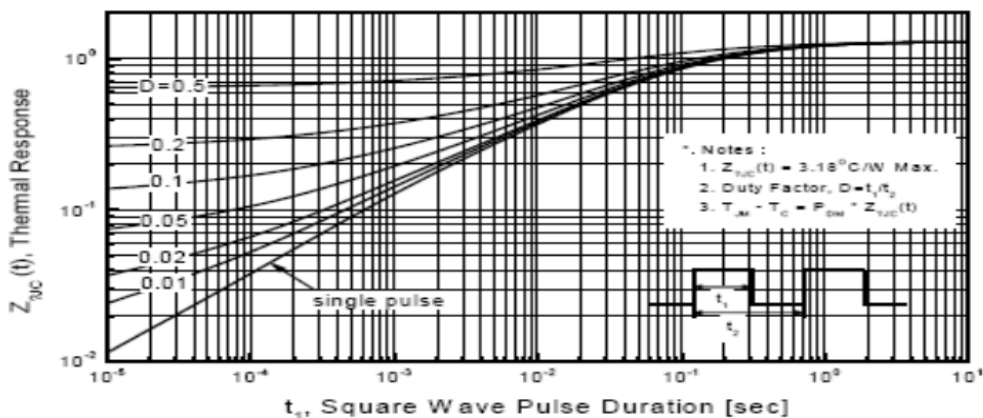


Fig 11. Transient Thermal Response Curve(TO220)



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Fig. 12. Gate Charge Test Circuit & Waveforms

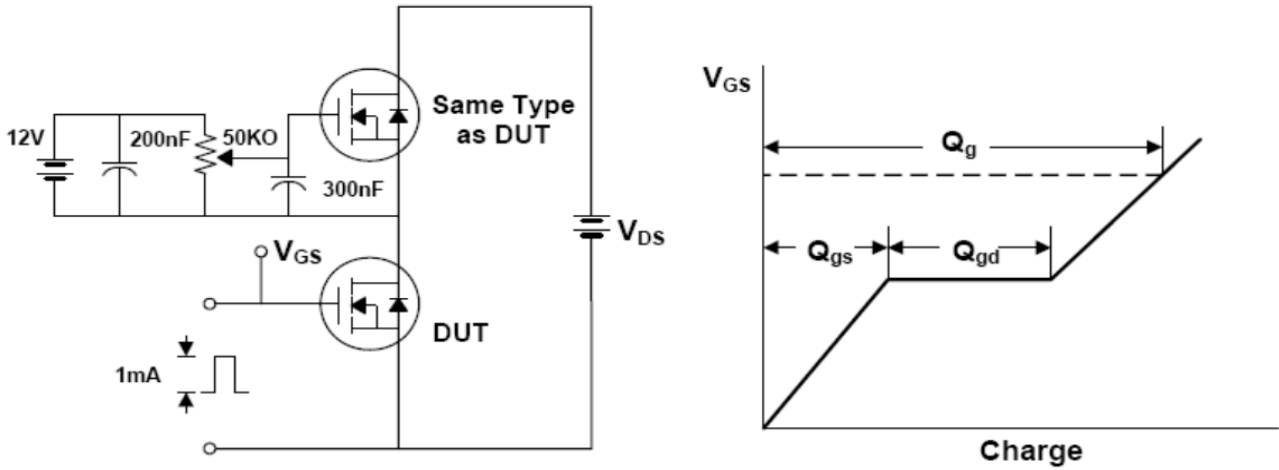


Fig 13. Switching Time Test Circuit & Waveforms

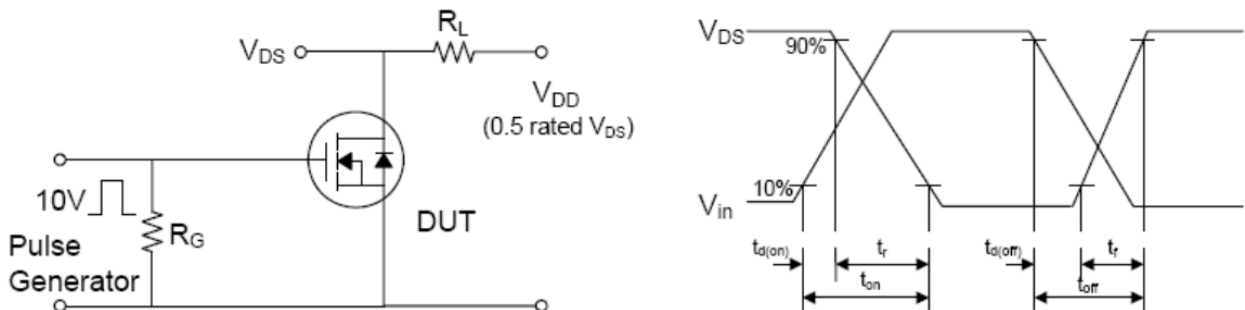
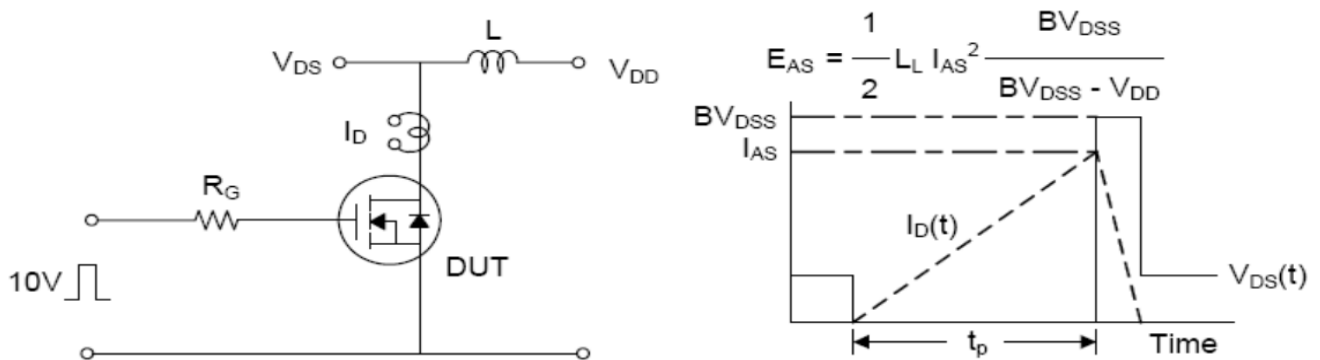


Fig 14. Unclamped Inductive Switching Test Circuit & Waveforms



CHARACTERISTIC CURVE

Fig. 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

